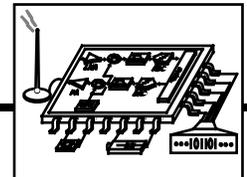


# **A Multi-Standard Monolithic CMOS RF Transceiver**

**Thomas Cho, Jacques Rudell, Jeff Ou,  
Todd Weigandt, Sekhar Narayanaswami,  
Srenik Mehta, George Chien,  
Carrol Barrett, Francesco Brianti\*,  
and Prof. Paul Gray.**

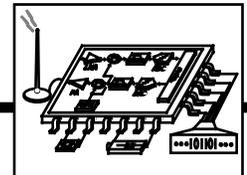
**University of California, Berkeley  
\*SGS Thomson**



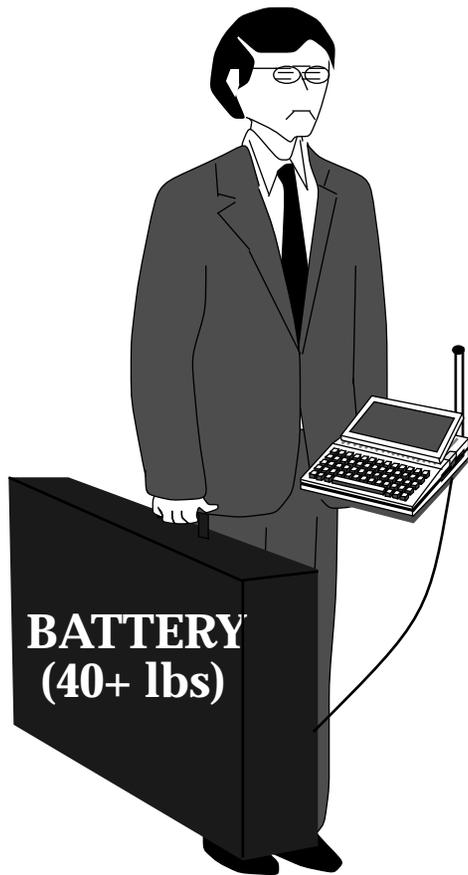
# Outline

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- **Background/Motivation**
- **A monolithic CMOS RF transceiver**
- **Design considerations**
- **Key building blocks**
- **Future plan**



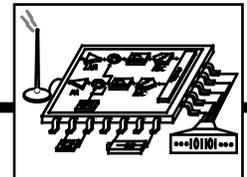
# Low Power Terminal Design



- Architecture Optimization
- Low-Power RF Design
- Low-Power ADC/DAC
- Low-Power Digital and DSP
- Power-Optimized Display
- Etc



**Next Step:  
Multi-Standard, Adaptive Modes of Communication**



# Overall Objective

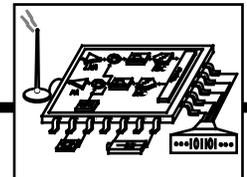
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**Single RF Modem with interface capability to:**

- **Public Cellular Network**
- **Cordless Phones/PBXs**
- **Wireless LANs**
- **Other emerging PCS Systems**

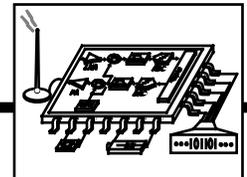
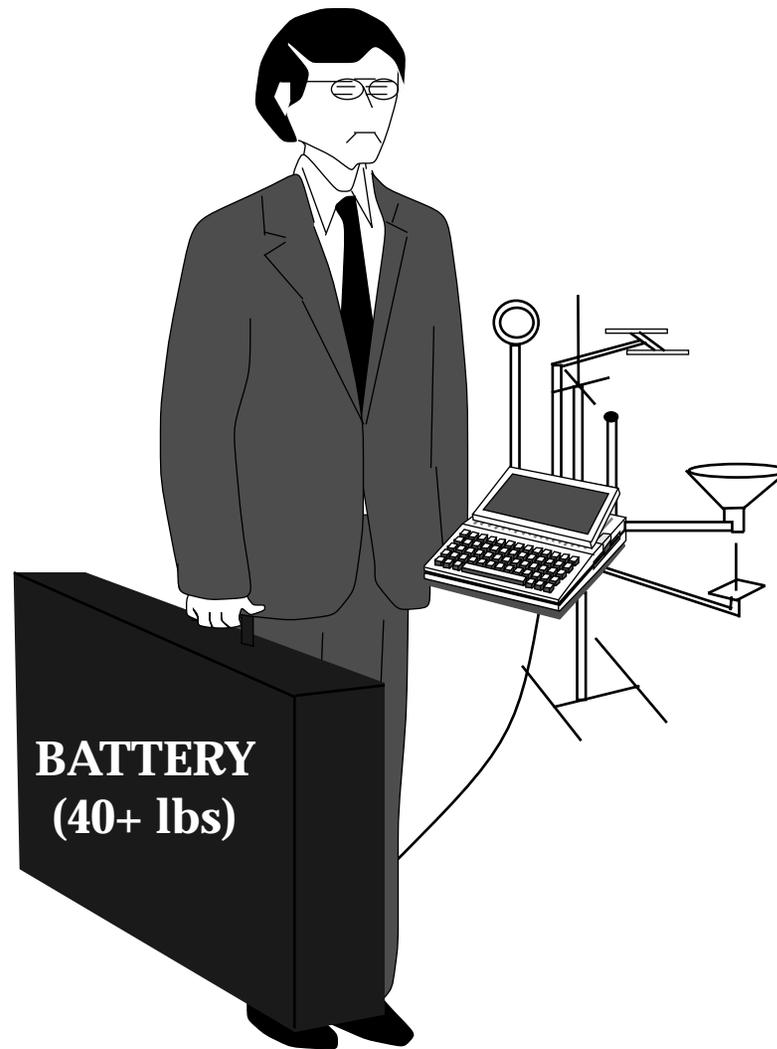
**Focus of this research:**

- **What are the important technical problems from the perspective of the RF modem design?**



# Adaptive, Multistandard RF Modems

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# Motivation

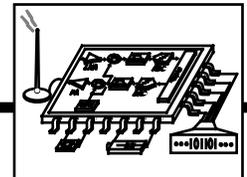
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## Design Goal:

- Radio transceiver for personal communications.

## Design Objectives:

- Low power consumption
- Low cost implementation
- Multi-Standard capability



# Research Goals

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- **Single-chip implementation**

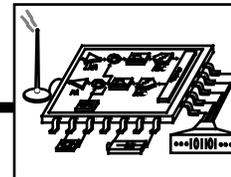
**Integrate both RF & Baseband circuits on the same chip**

**Eliminate off-chip high frequency signal paths to reduce off-chip components for low power, low cost & smaller form factors (ext. LC-tank, ext. IF BPF, ..)**

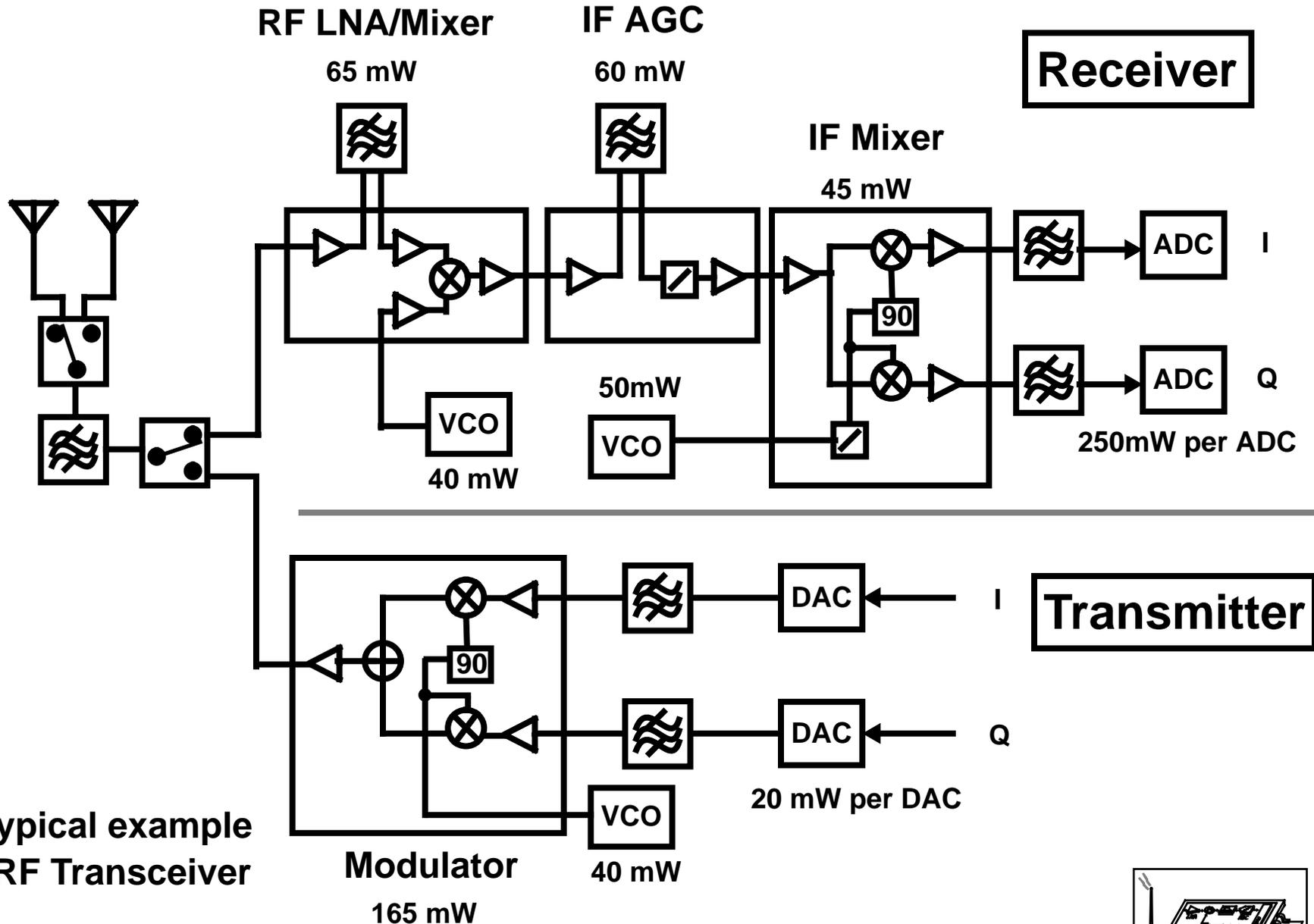
**Baseband digital signal processing for programmable multistandard capability**

- **CMOS technology**

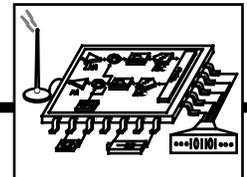
**High integration and low cost**



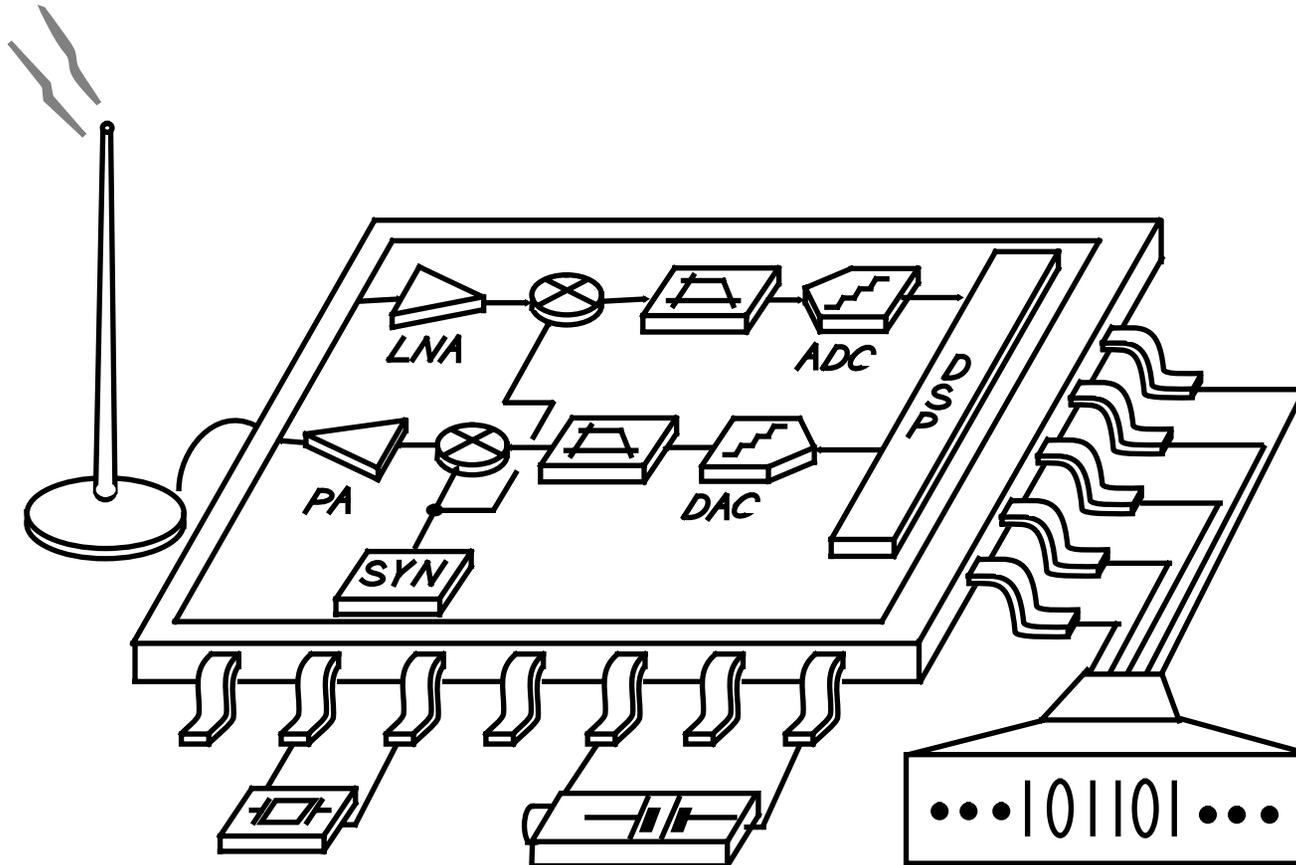
# Conventional Approach



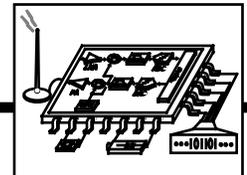
A typical example of RF Transceiver



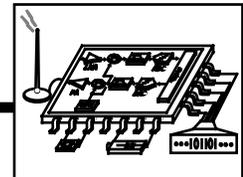
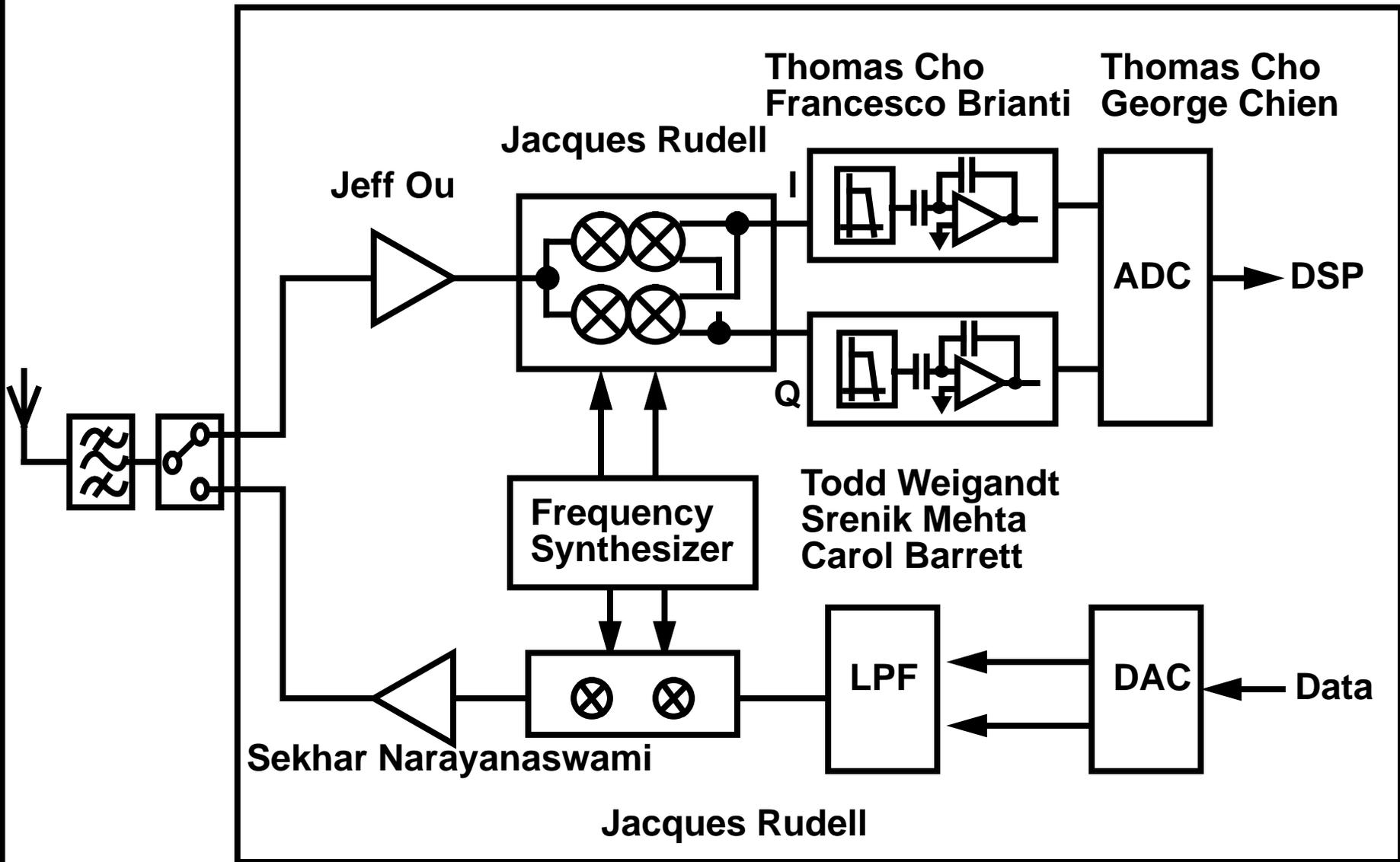
# Our Approach



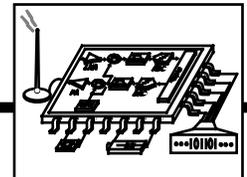
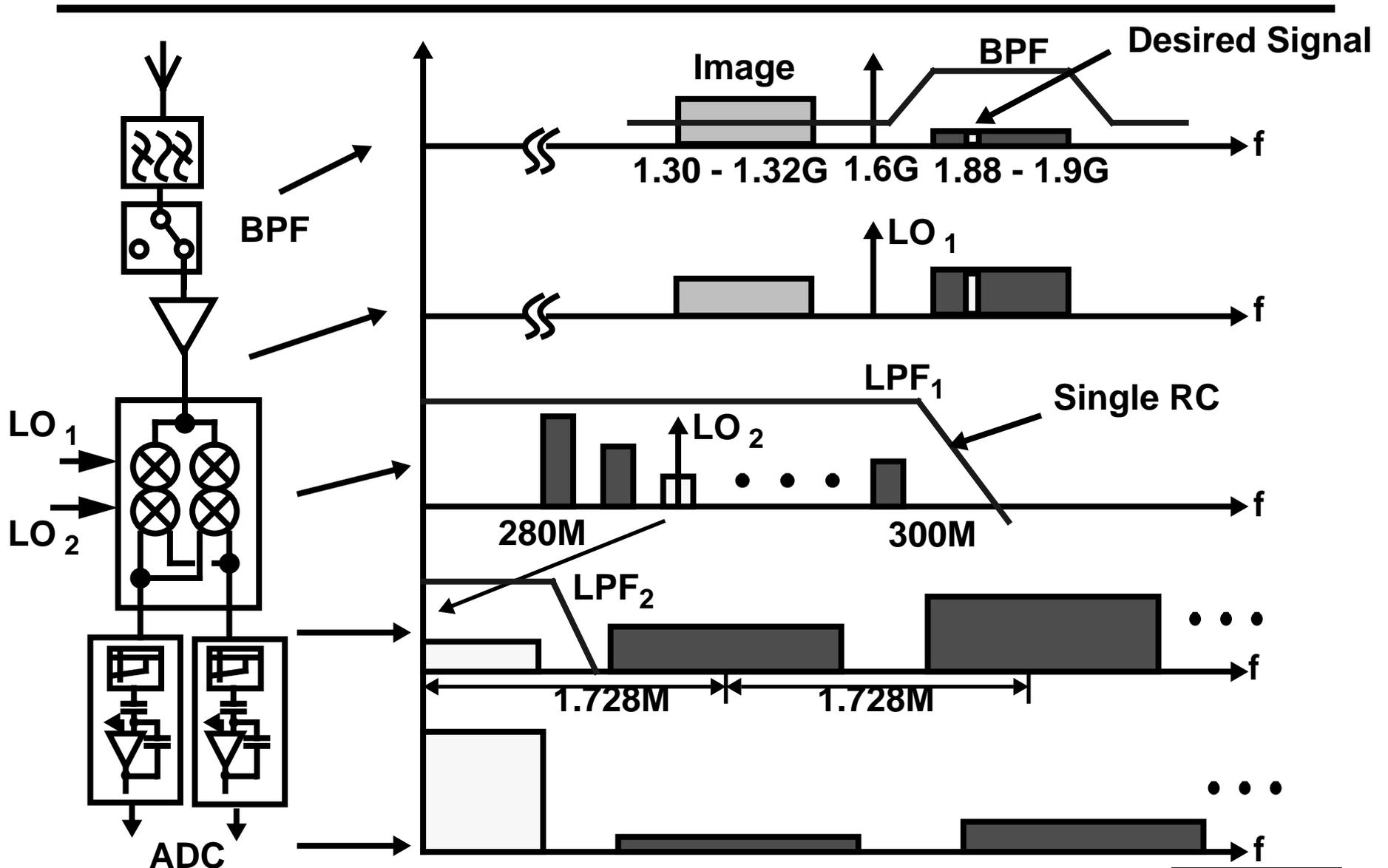
- Using DECT standard as a vehicle to study various problems/issues



# A Quasi-Direct Conversion Approach

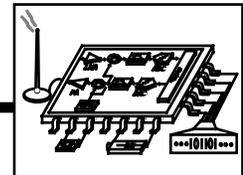
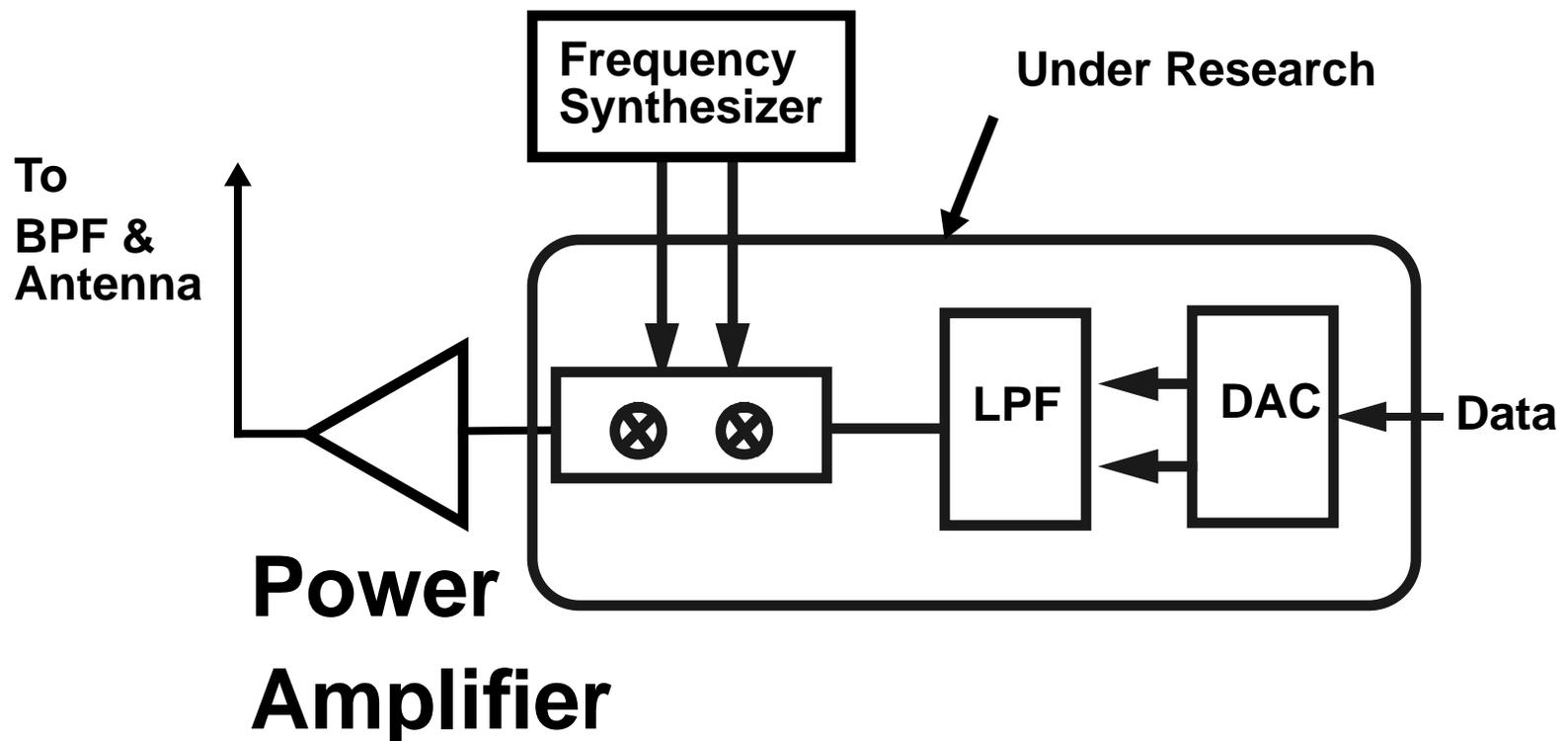


# Receiver Path (DECT)



# Transmitter Path (DECT)

- Power Amplifier(PA) design is near completion.
- Transmitter architecture still in early research phase

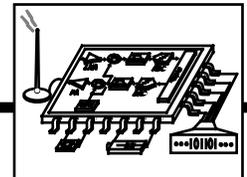


# What's different?

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## A Quasi-Direct Conversion Receiver

- **No external IF BPF**
    - ⇒ Little or No IF Filtering
    - ⇒ Selective filtering at Baseband
  - **Two Local Osc. freq's.**
    - LO<sub>1</sub> : a fixed freq. osc
    - LO<sub>2</sub> : a tuned osc to the desired channel
- ⇒ Elimination of carrier feedthrough compared to direct conversion arch.
- ⇒ Relaxed phase noise requirement on LO<sub>2</sub> (tuned osc).



# Design Challenges

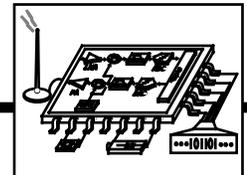
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- **System:**

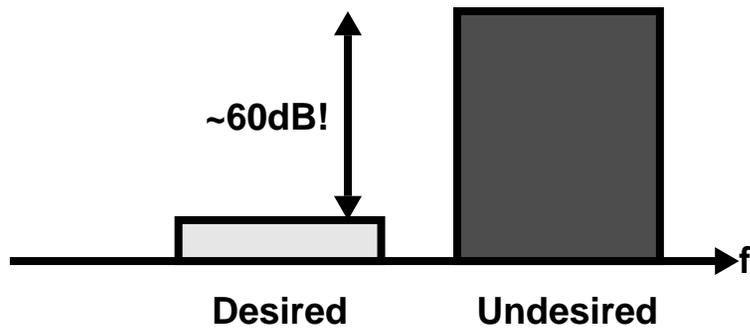
- **Data recovery in the presence of strong interferers and noise w/o ext. IF filters!**
- **Image-Reject Mixer required**
- **Low phase noise osc w/o ext. high-Q LC tank**

- **Circuit:**

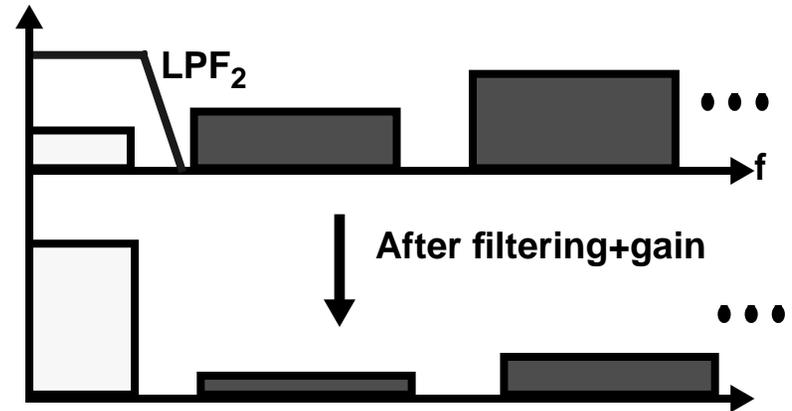
- **CMOS design**
- **Power efficient circuit topologies**
- **Low voltage design: 3.3V**



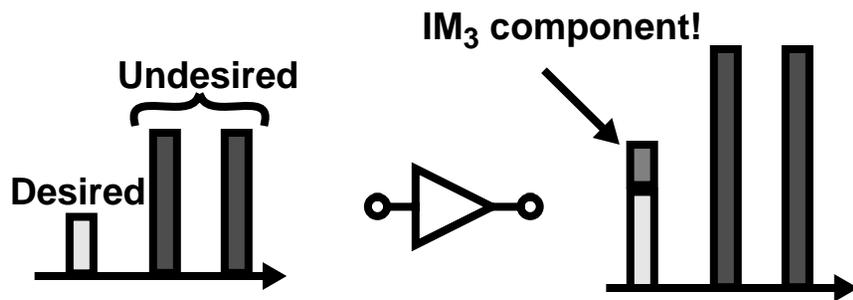
# Design Considerations (I): System



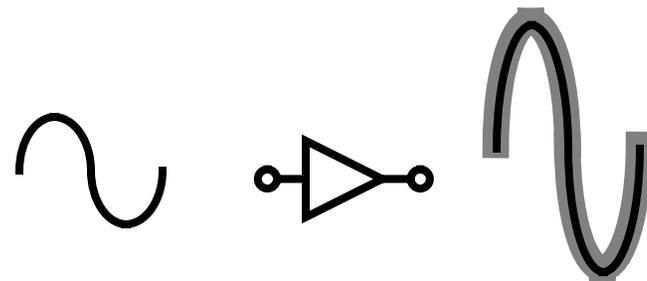
Proper signal level control along the receiver signal path



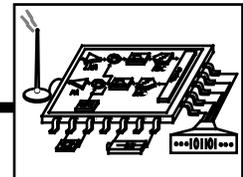
Baseband channel select filter/gain design



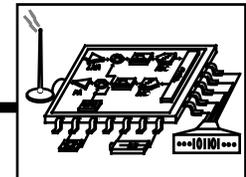
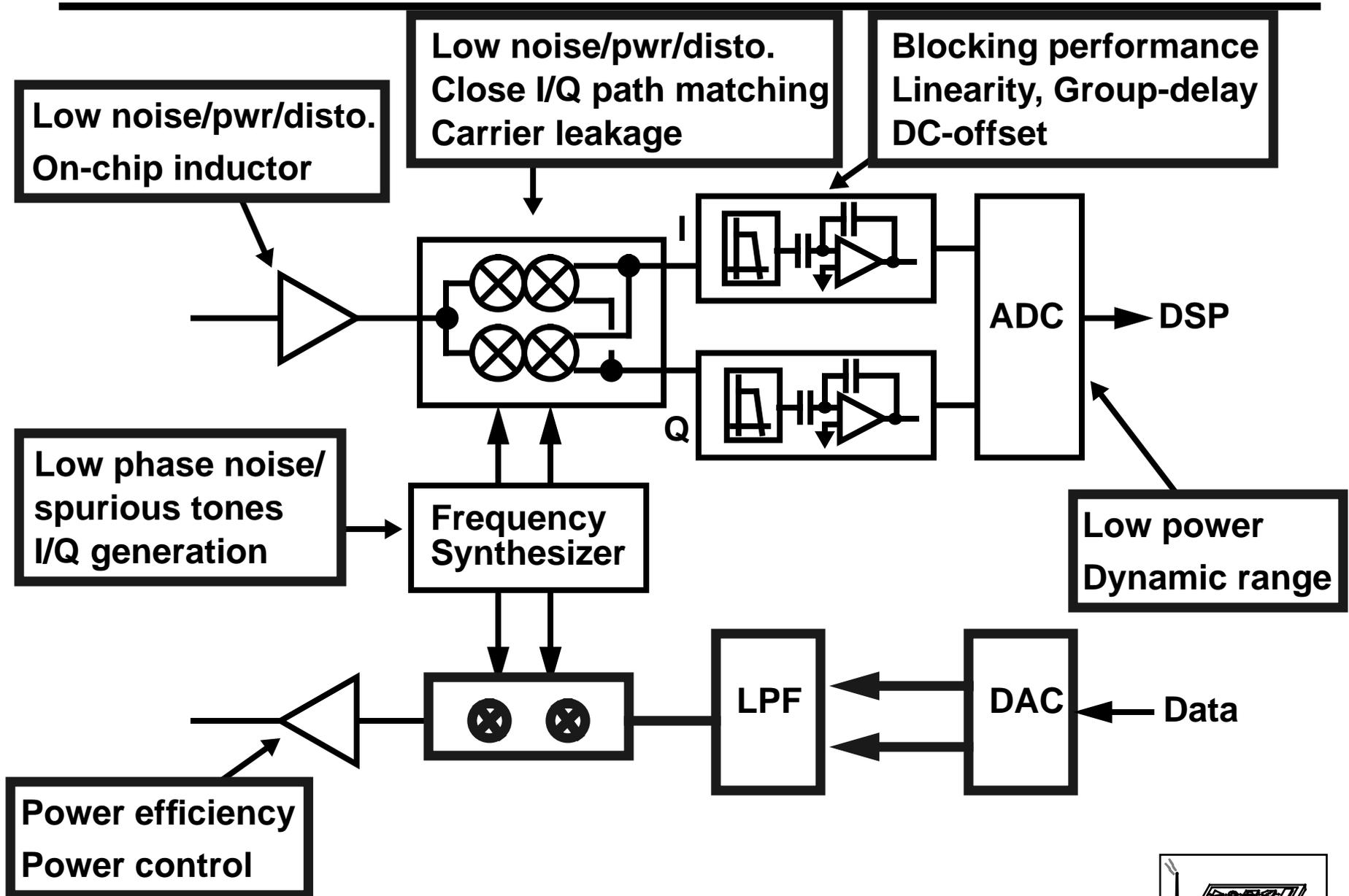
Distortion performance: Intermodulation(IM<sub>3</sub>)



Noise performance: Power vs. noise

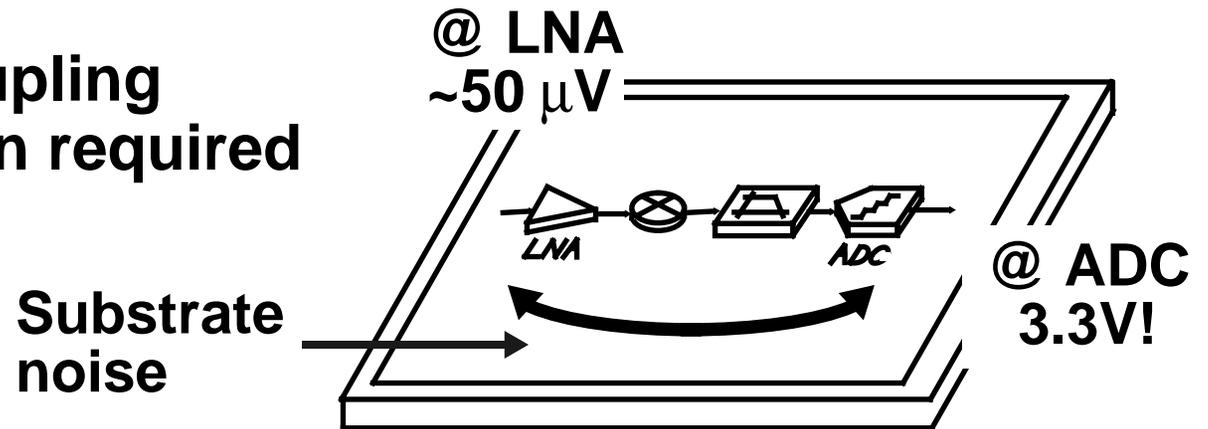


# Design Considerations (II):Block

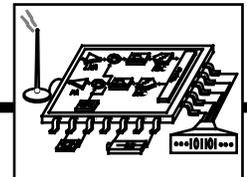
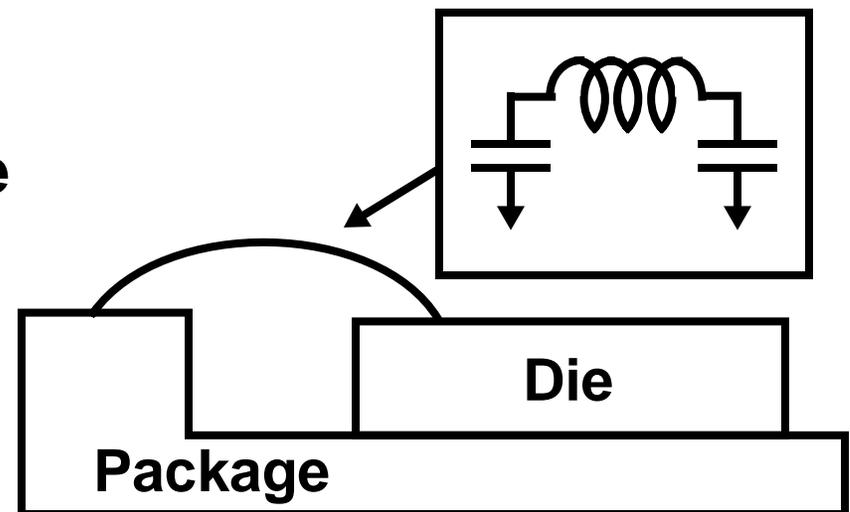


# Design Considerations (III): Others

- **Substrate noise coupling**  
- Noise isolation required



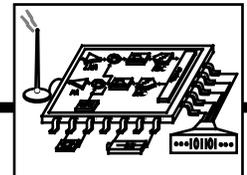
- **Package modelling**  
- Bond wire modelling for LNA & PA's I/O impedance matching



# Key Building Blocks

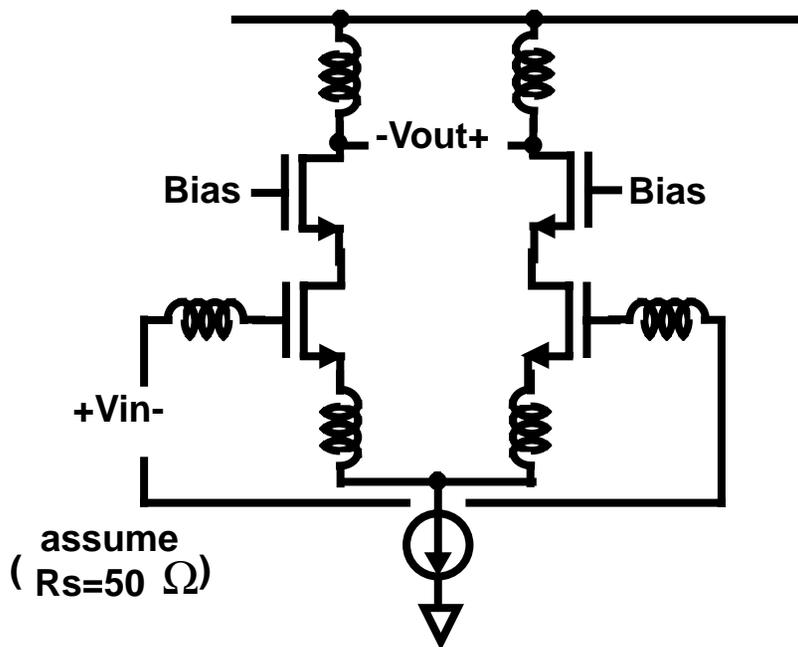
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- **LNA** : **Jeff Ou**
- **Image-Reject Mixer** : **Jacques Rudell**
- **Freq. Synthesizer** : **Todd Weigandt,  
Srenik Mehta, Carol Barrett**
- **Baseband Filter  
/Gain** : **Thomas Cho,  
Francesco Brianti**
- **A/D Converter** : **Thomas Cho,  
George Chien**
- **PA** : **Sekhar Narayanaswami**

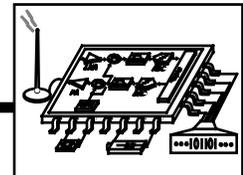


# RF Low Noise Amplifier

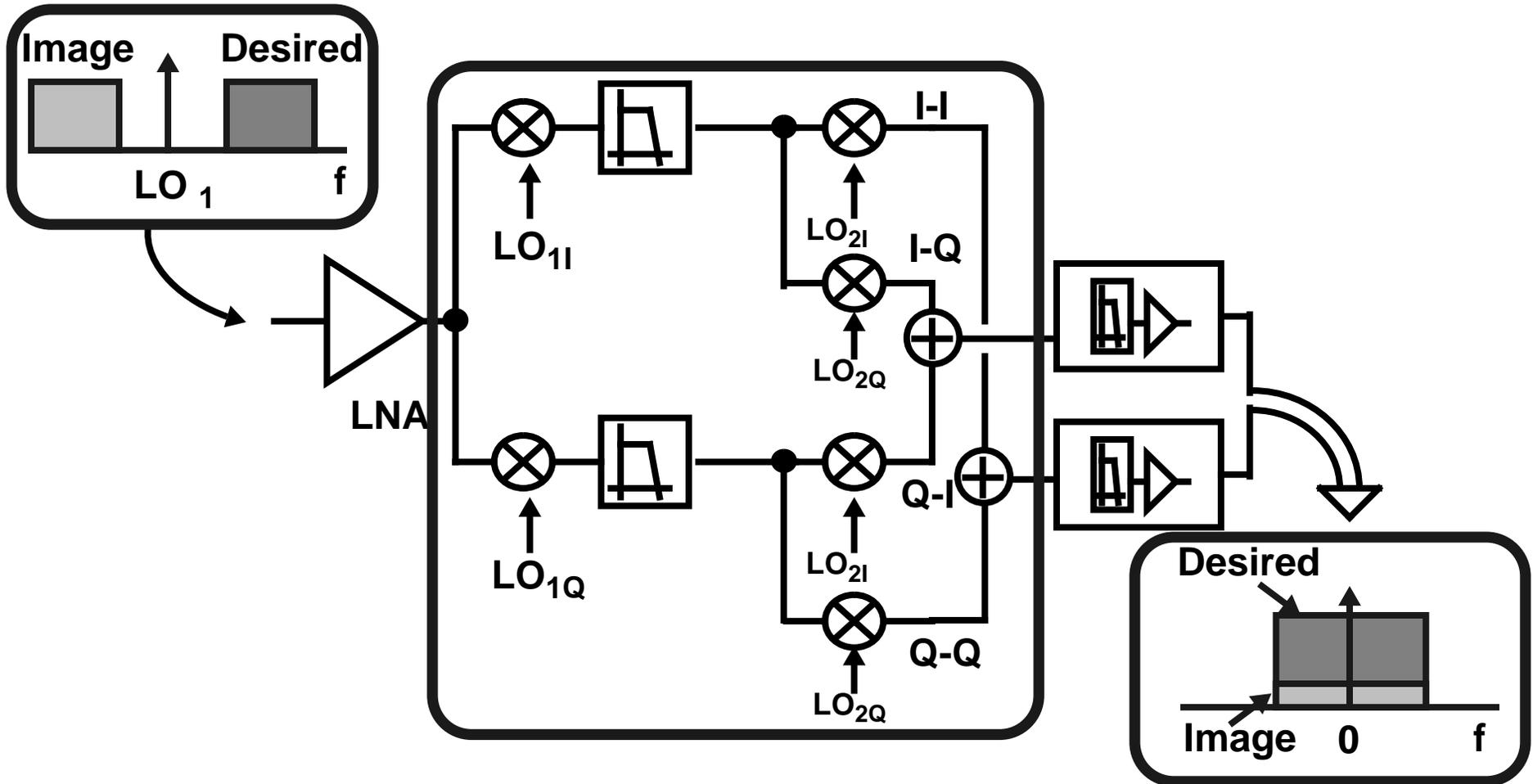
- A single-stage differential-mode amplifier
- On-chip spiral inductors for input impedance matching and output load tuning
- Critical Issues: Modelling of spiral inductors, Package modelling..



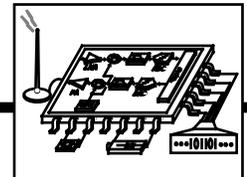
**Noise Figure: 2.1 dB**  
**Gain: 20dB @ 1.9GHz**  
**IP3: -2 dBm (input)**  
**Power: 20mW @ 3V**  
**Tech: 0.6  $\mu$ m CMOS**



# Image-Reject Mixer

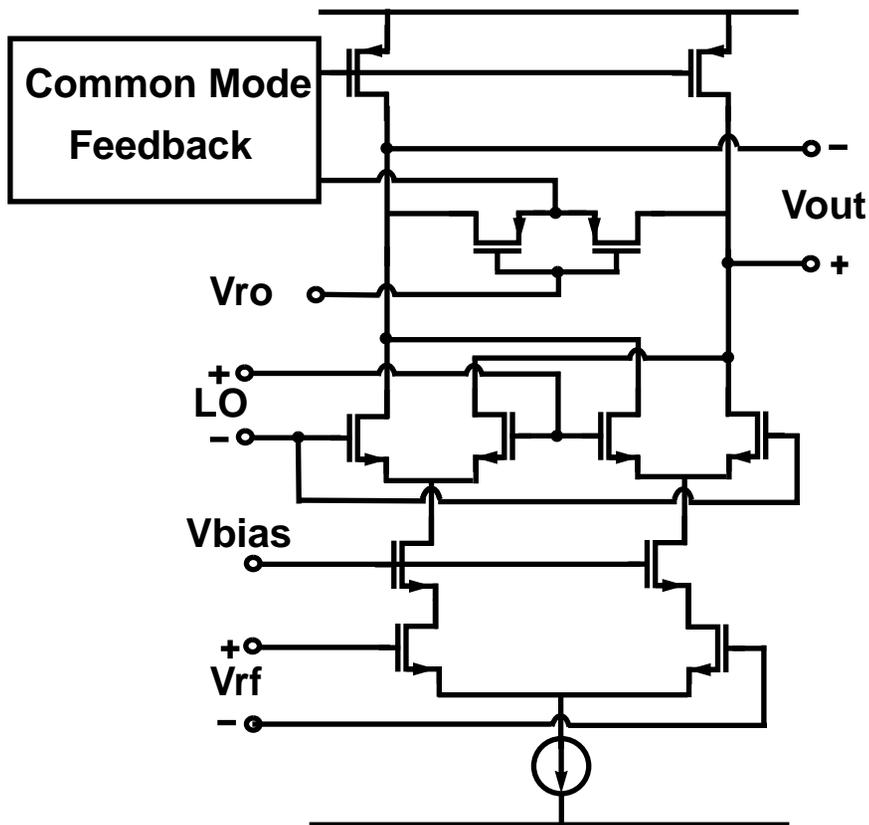


- Extra 35dB of image rejection required due to insufficient image rejection from RF BPF



# Image Reject Mixer Cell

- Gilbert Cell Based Topology.
- Variable Gain via  $V_{ro}$ .
- Cascode stage to isolate input stage from the Local Osc.

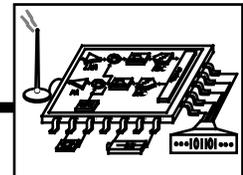


$IP_3$  : 10dBm.

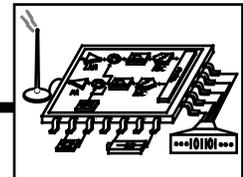
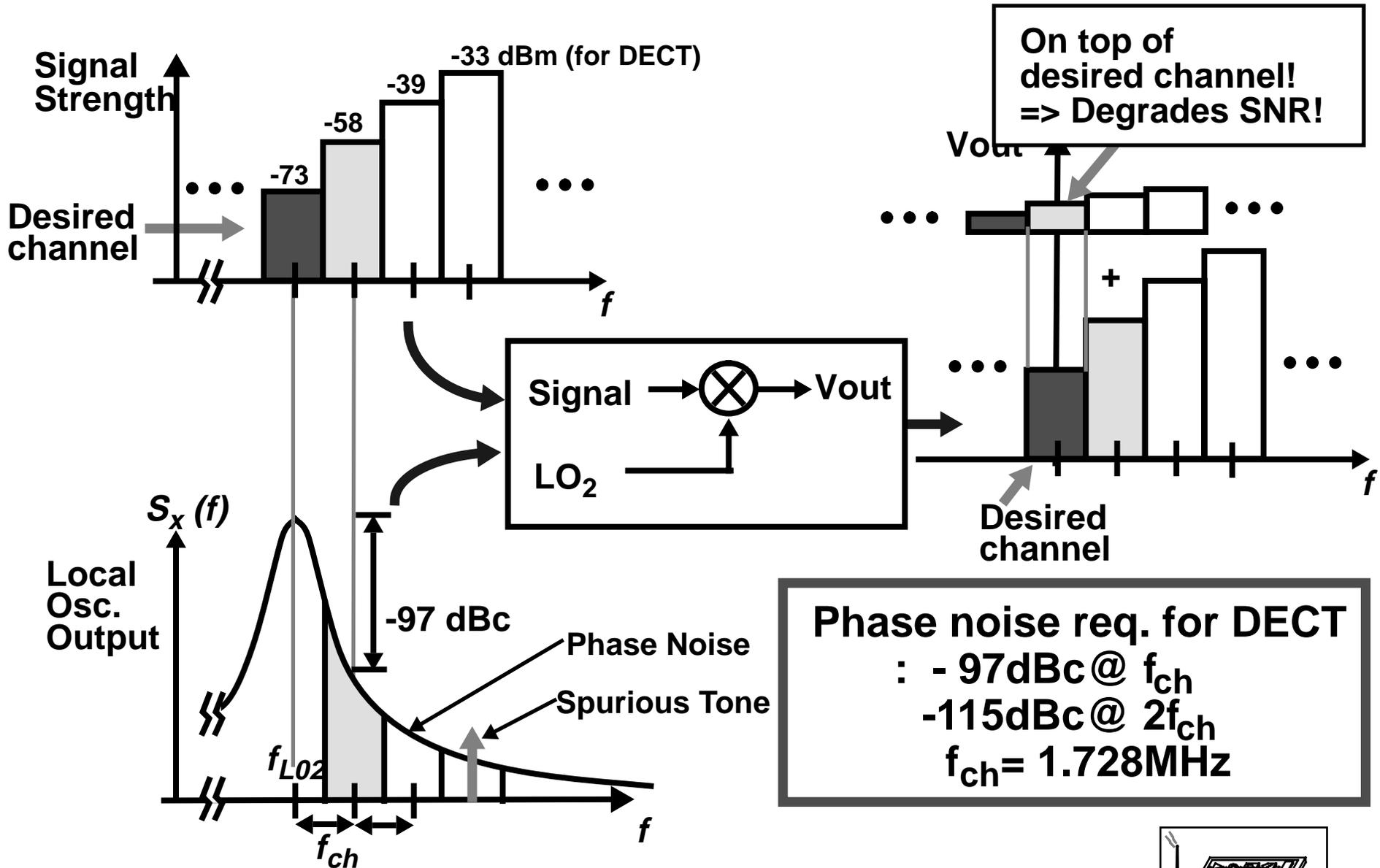
Variable Gain : 10dB ~ 35dB

Image-Rejection: ~35dB

Total Power : 40mW

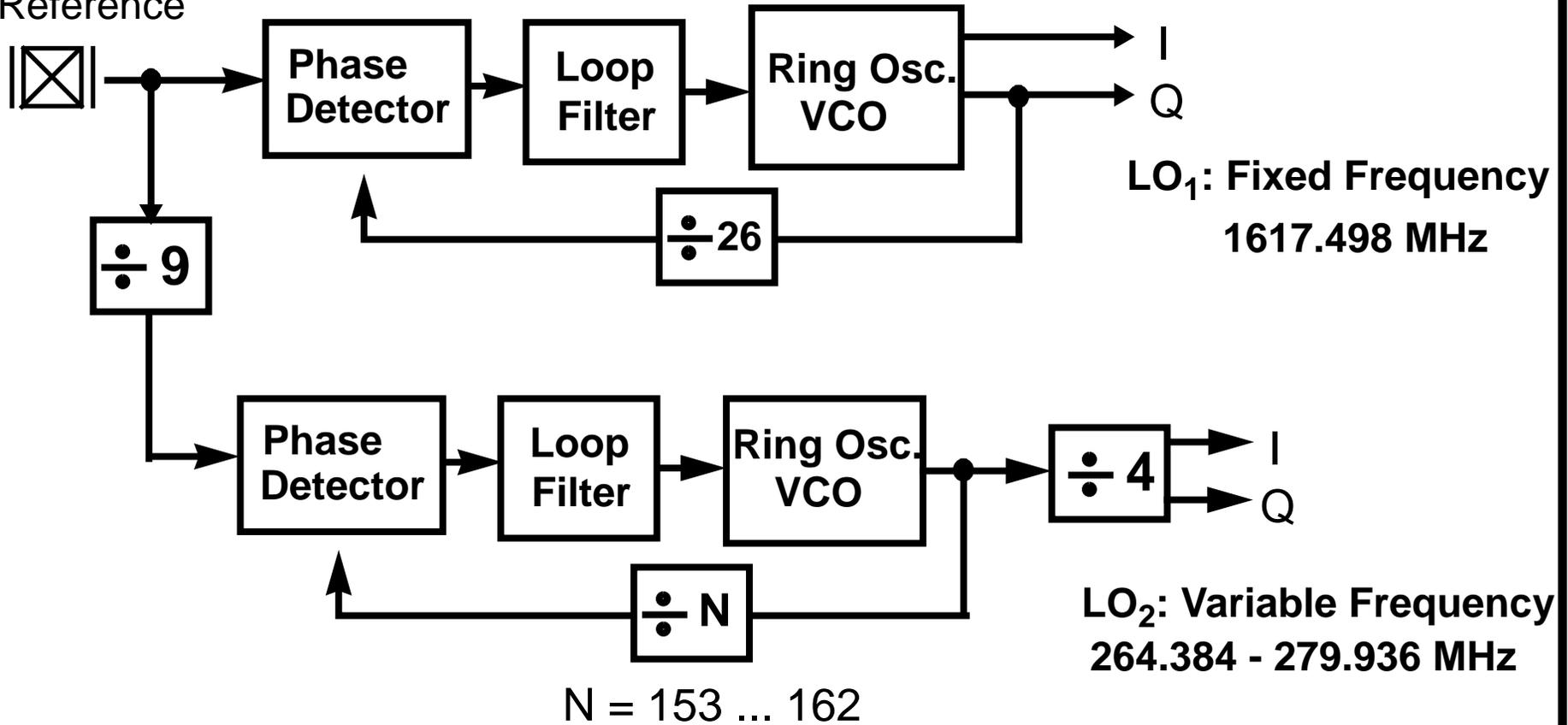


# Freq. Synthesizer(I): Phase Noise Req.

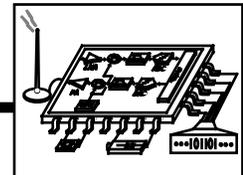


# Freq. Synthesizer(II): for DECT

Crystal Reference 62.208 MHz

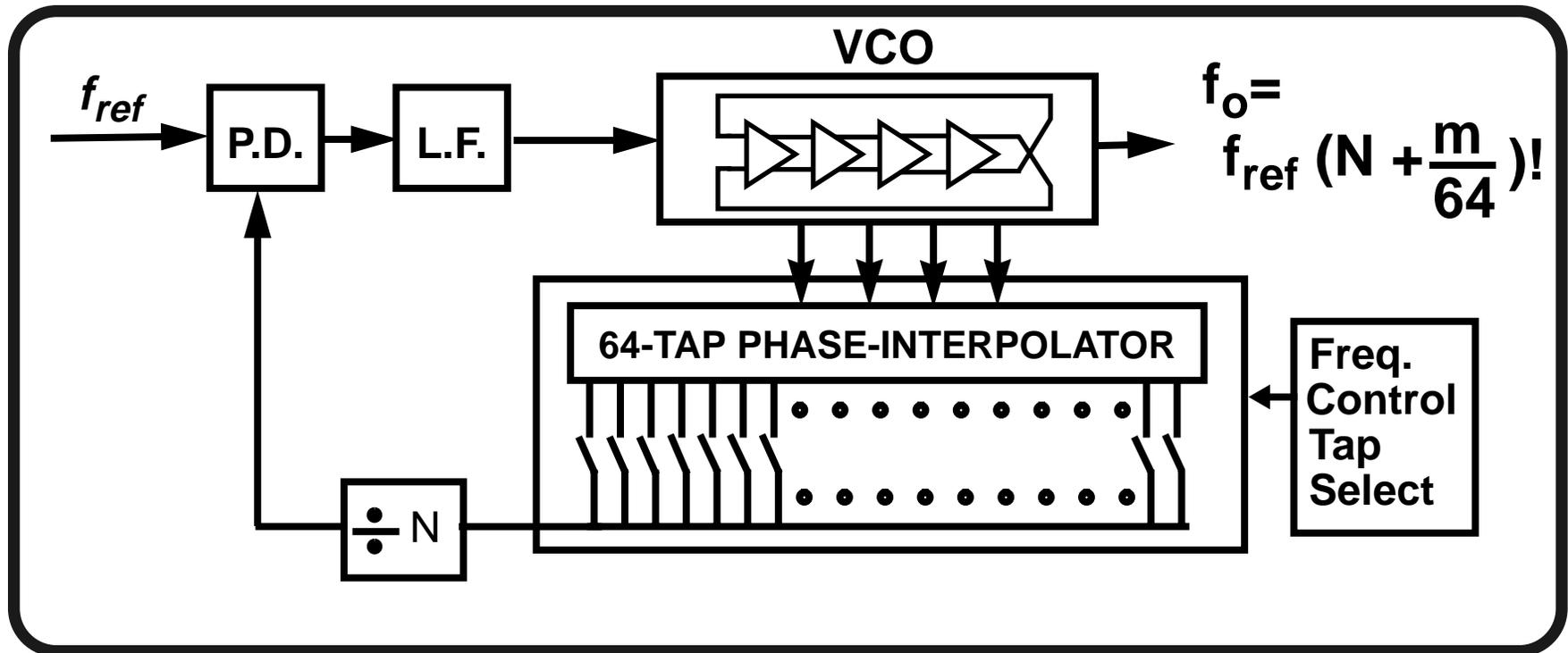


DECT Channel Spacing = 1.728 MHz

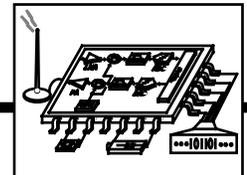


# Freq. Synthesizer(III): for Multistandard

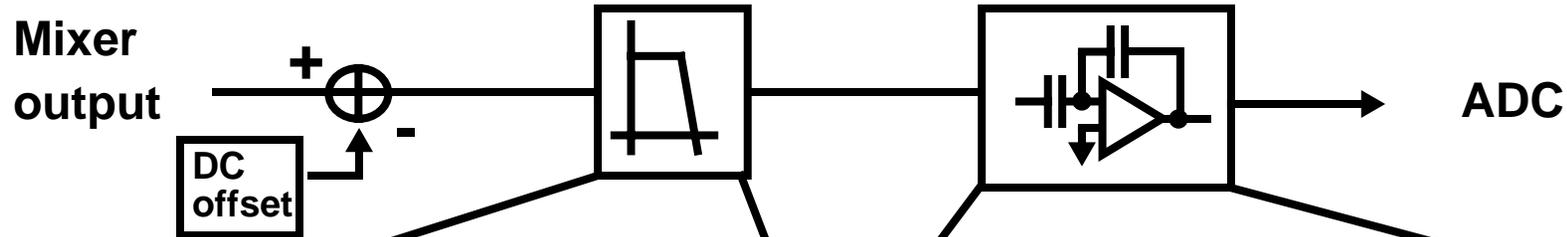
Channel Spacing : DECT 1.728 MHz  
Other Standards (FDMA) 10 KHz, 30 KHz, 200 KHz



- **PHASE INTERPOLATED FREQ. SYNTHESIZER** for finer channel spacings while maintaining high ref. freq. and high PLL bandwidth.



# Baseband Filter/Gain Stage



## ● Anti-aliasing Filter:

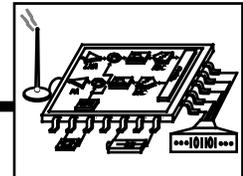
**Sallen-Key  
continuous-time LPF**

- Out-of-DECT-Band signal rejection
- BW =  $\sim 2\text{MHz}$
- $\sim 4\text{-}5\text{th}$  order
- DC offset correction

## ● Channel Selection Filter:

**Switched capacitor  
sampled-data LPF + Gain**

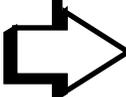
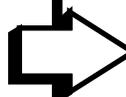
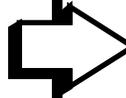
- Adjacent channel rejection
- constant group delay
- BW =  $\sim f_{\text{data}}/2$
- 6th order ( $f_s = 18x$ )  
+ 3rd order Phase eq.



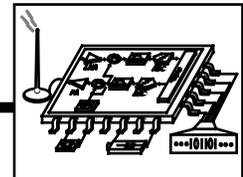
# A/D Converter

## A 10-bit 20MS/s 35mW Pipeline ADC\*

The Next Generation of 10 bit 20MS/s CMOS ADC

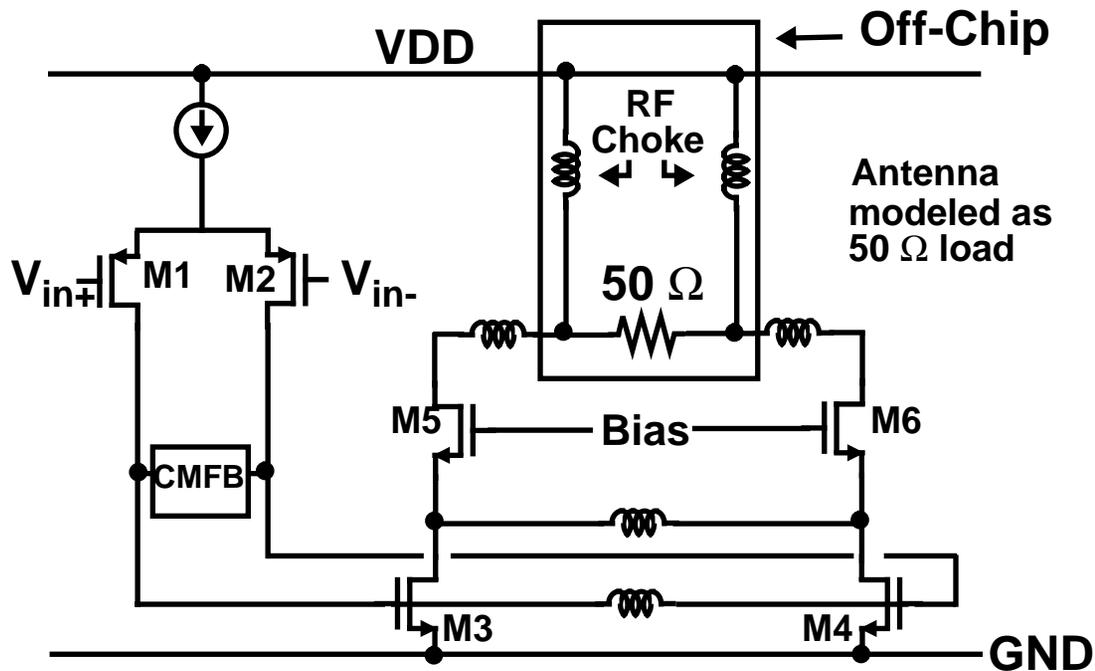
Tech	1.2 $\mu$ m		0.6 or 0.8 $\mu$ m
Vdd	3.3V		3.3V
Active Area	3.2x3.3 mm <sup>2</sup>		~1.5x1.5 mm <sup>2</sup>
Power	35mW @ 20MS/s		~10mW @ 20MS/s

\*:T. Cho & P. Gray  
@CICC 94, San Diego



# RF Power Amplifier

- A two-stage differential-mode amplifier
- On-chip spiral inductors for tuning out gate capacitance and output impedance matching
- Require power control

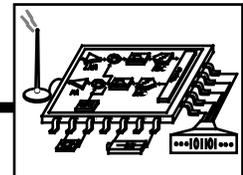


**Output Power:**

**250mW @ 1.9GHz**

**Efficiency: > 30%**

**Tech: 0.6  $\mu\text{m}$  CMOS**



# Future Plan

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- **Tape out 1st version : Spring, 1995**
  - Individual blocks
  - The whole receiver channel
- **Testing/Evaluation : Summer, 1995**
- **Tape out 2nd version : Winter, 1995**
  - Both receiver/transmitter channels

